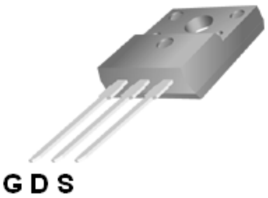
RoHS Compliant

P0908ATF

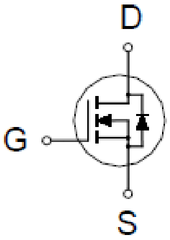
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
80V	9mΩ @V_{GS} = 10V	43A



TO-220F



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[2]	T_C = 25 °C	I_D	43	A
	T_C = 100 °C		27	
Pulsed Drain Current[1,2]		I_{DM}	160	
Avalanche Current		I_{AS}	38	
Avalanche Energy	L = 0.1mH	E_{AS}	72	mJ
Power Dissipation	T_C = 25 °C	P_D	37	W
	T_C = 100 °C		15	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3.3	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1] Pulse width limited by maximum junction temperature.

[2] Limited only by maximum temperature allowed.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250µA	80			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250µA	2	3.4	4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 64V, V_{GS} = 0V			1	µA
		V_{DS} = 60V, V_{GS} = 0V , T_J = 125 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 7V, I_D = 15A		8.1	12	mΩ
		V_{GS} = 10V, I_D = 20A		7	9	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 20A		57		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		2853		pF
Output Capacitance	C_{oss}			355		
Reverse Transfer Capacitance	C_{rss}			199		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		0.9		Ω
Total Gate Charge[2]	Q_g V_{GS} = 10V	V_{DS} = 40V,V_{GS} = 10V, I_D = 20A		55		nC
	V_{GS} = 7V			41.5		
Gate-Source Charge[2]	Q_{gs}			15.3		
Gate-Drain Charge[2]	Q_{gd}			19.4		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 40V, I_D ≅ 20A, V_{GS} = 10V, R_{GEN} = 6Ω		37		nS
Rise Time[2]	t_r			45		
Turn-Off Delay Time[2]	$t_{d(off)}$			61		
Fall Time[2]	t_f			42		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				26	A
Forward Voltage[1]	V_{SD}	I_F = 20A, V_{GS} = 0V			1.4	V
Reverse Recovery Time	t_{rr}	I_F = 20A , dI_F/dt= 100A/µs		34		nS
Reverse Recovery Charge	Q_{rr}			37		nC

[1] Pulse test : Pulse Width ≤ 300 µsec, Duty Cycle ≤ 2%.

[2] Independent of operating temperature.

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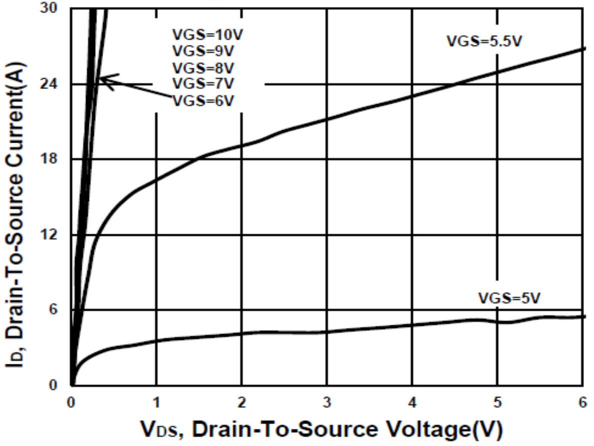
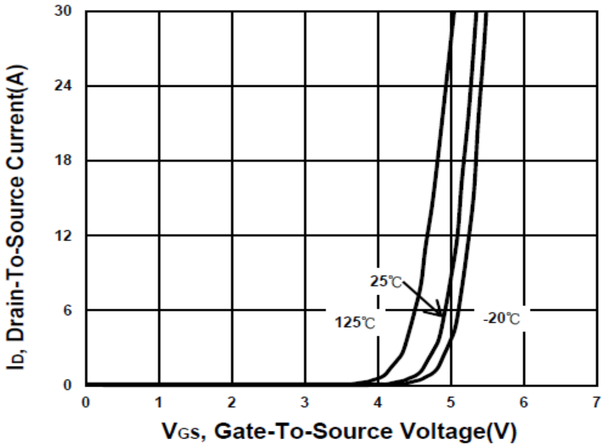
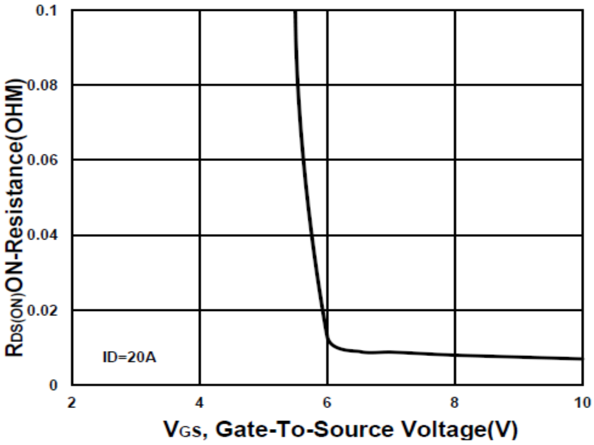
Output Characteristics



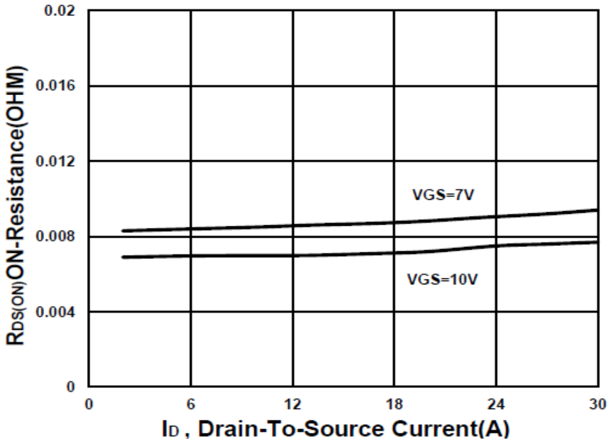
Transfer Characteristics



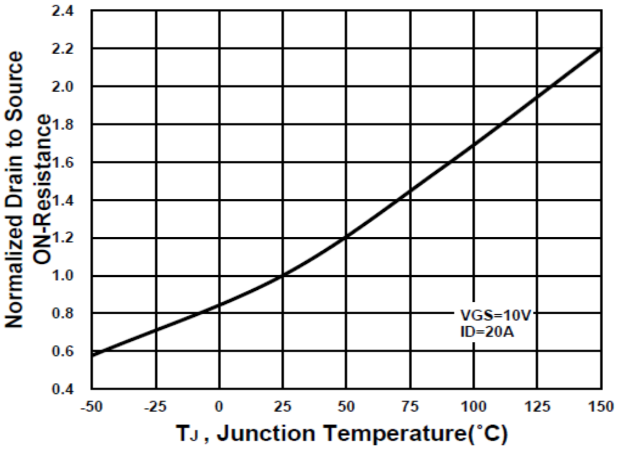
On-Resistance VS Gate-To-Source



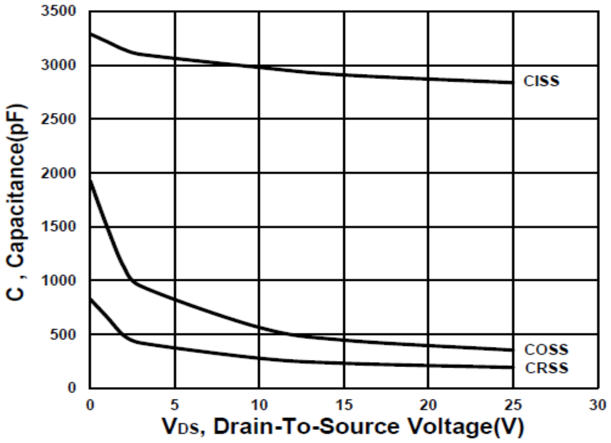
On-Resistance VS Drain Current



On-Resistance VS Temperature



Capacitance Characteristic



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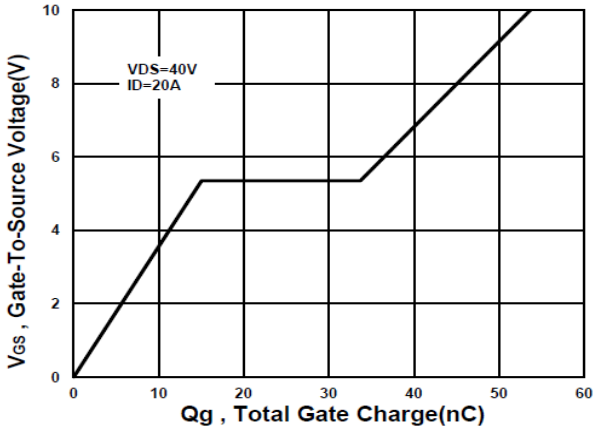
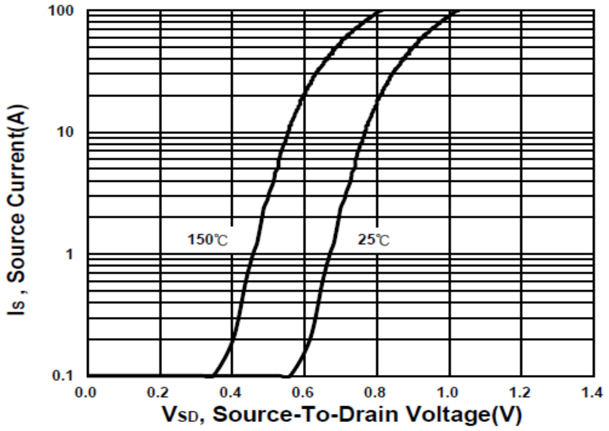
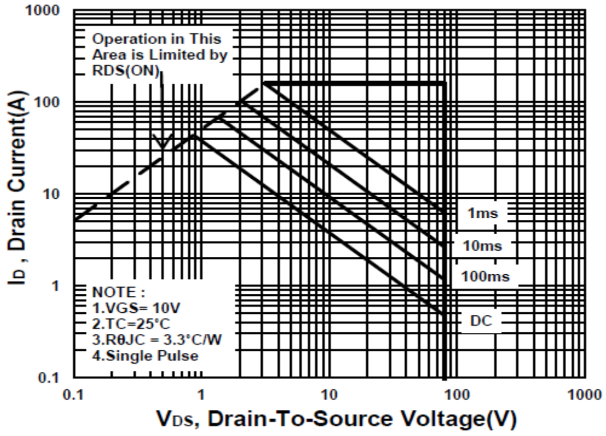
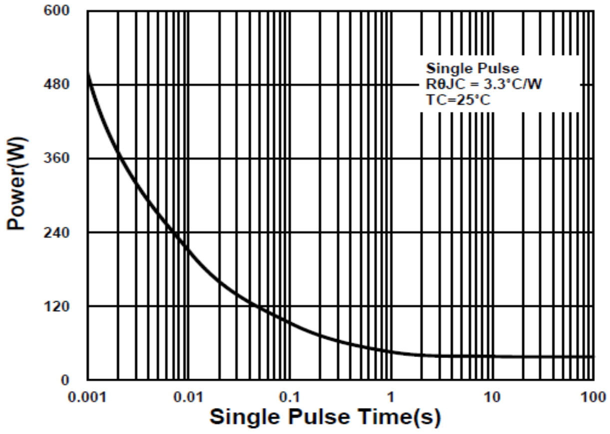
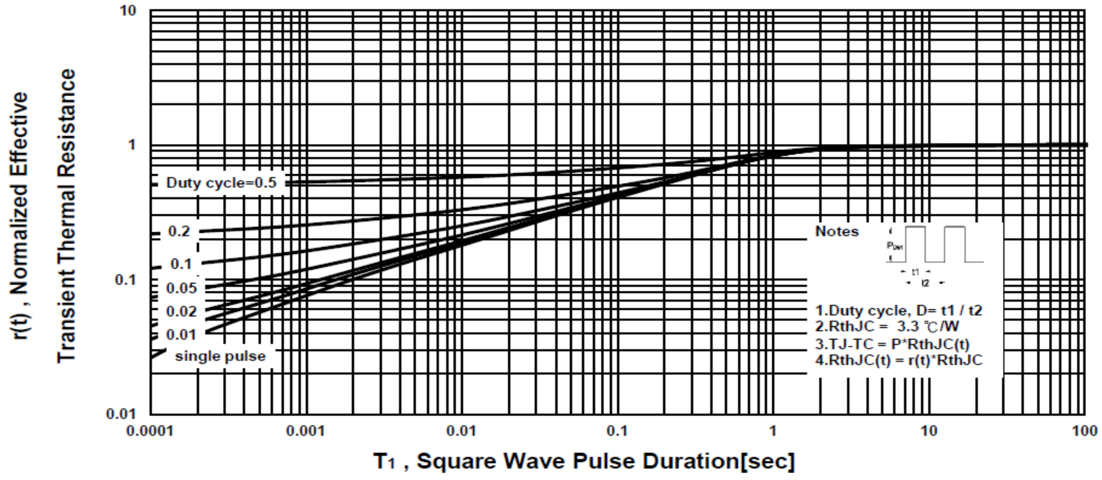

Gate charge Characteristics


Source-Drain Diode Forward Voltage


Safe Operating Area

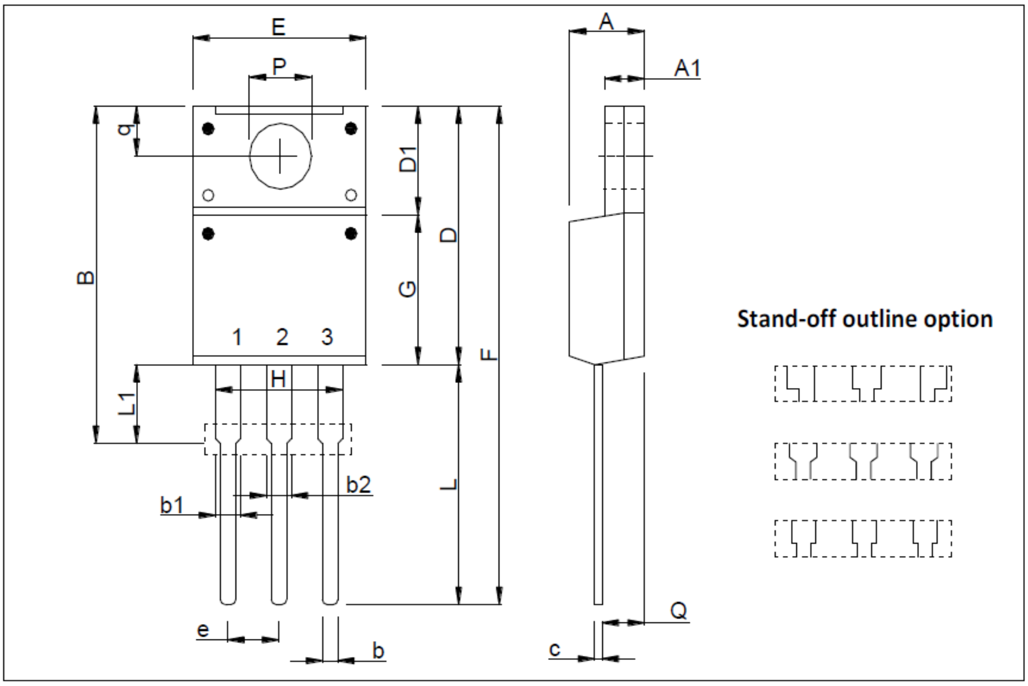

Single Pulse Maximum Power Dissipation


Transient Thermal Response Curve

Package Dimension

TO-220F (3-Lead) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.4		4.93	e	2.34		2.74
A1	2.34		3.1	F	27.2		30.6
B	18.8		20	G	7.7		9.39
b	0.65		1	H	6.18		6.82
b1	0.93		1.6	L	12.7		14.2
b2	0.95		1.6	L1	2.88		3.7
c	0.4		1	P	2.98		3.7
D	13.5		16.4	Q	2.3		2.96
D1	6.48		6.95	q	3.1		3.8
E	9.8		10.4				



*因各家封装模具不同而外观略有所差异，不影响电性及Layout。

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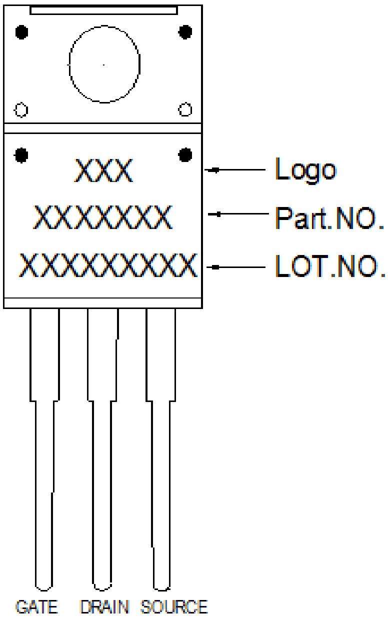
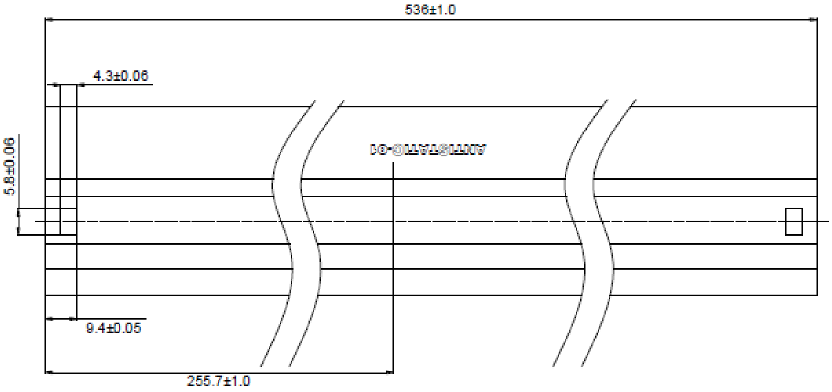
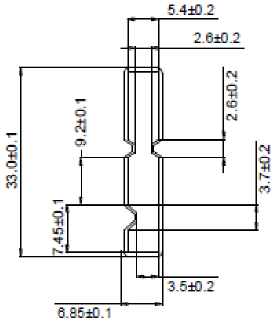
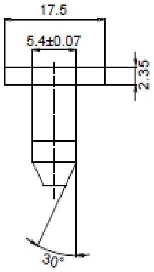
A. Marking Information

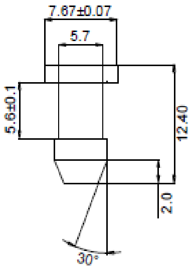


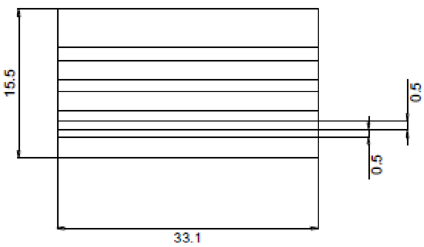
B. Tape&Reel Information:50pcs/Tube(2000pcs/Box)

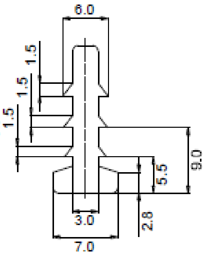






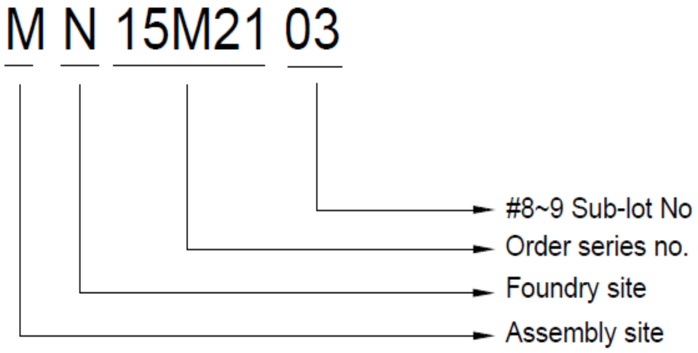






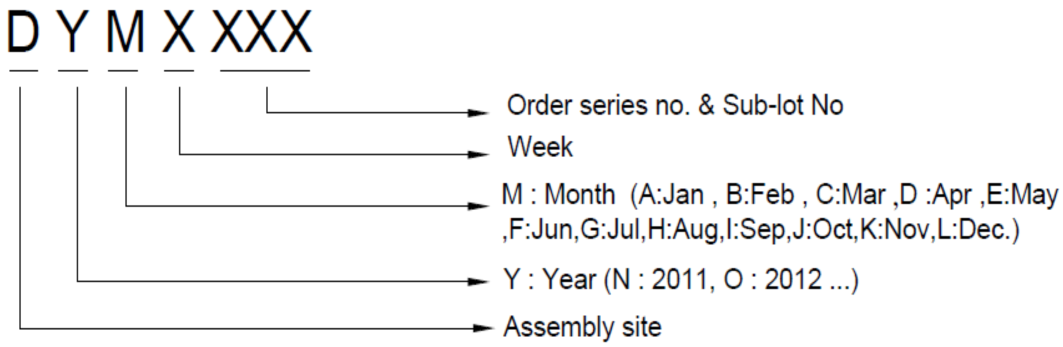
C. Lot.No. & Date Code rule

1.LOT.NO.



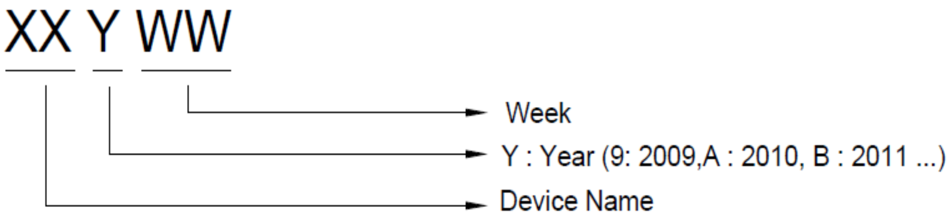
#8~9 Sub-lot No
Order series no.
Foundry site
Assembly site

2.Date Code



Order series no. & Sub-lot No
Week
M : Month (A:Jan , B:Feb , C:Mar ,D :Apr ,E:May ,F:Jun,G:Jul,H:Aug,I:Sep,J:Oct,K:Nov,L:Dec.)
Y : Year (N : 2011, O : 2012 ...)
Assembly site

3.Date Code (for Small package)



Week
Y : Year (9: 2009,A : 2010, B : 2011 ...)
Device Name

D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文”O” 和数字”0” ，”G 和”Q” 的字型即可)
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least